
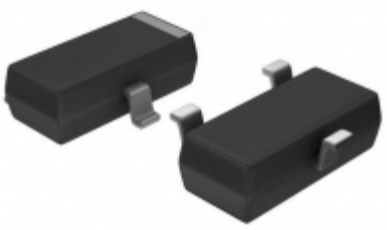



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|---|---|
|  | <p>Hersteller-Teilenummer: SI2319DS-T1-GE3</p> |
| | <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> |
|  | <p>Teil der Beschreibung: MOSFET P-CH 40V 2.3A SOT23-3</p> |
| | <p>Datenblätter:  SI2319DS-T1-GE3.pdf</p> |
| | <p>RoHs Status: Bleifrei / RoHS-konform</p> |
| | <p>Lagerzustand: New original, 84929 pcs Stock Available.</p> |
| | <p>Liefern von: Hong Kong</p> |
| <p>Image may be representation. See specs for product details.</p> | <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |

Spezifikationen

| | |
|--|--|
| Teilenummer | SI2319DS-T1-GE3 |
| Hersteller | Electro-Films (EFI) / Vishay |
| Beschreibung | MOSFET P-CH 40V 2.3A SOT23-3 |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 84929 pcs Stock |
| Hersteller Standard Vorlaufzeit | 33 Weeks |
| detaillierte Beschreibung | P-Channel 40V 2.3A (Ta) 750mW (Ta) Surface Mount |
| Serie | TrenchFET® |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-236-3, SC-59, SOT-23-3 |
| Verlustleistung (max) | 750mW (Ta) |
| Typ FET | P-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 40V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 2.3A (Ta) |
| Rds On (Max) @ Id, Vgs | 82 mOhm @ 3A, 10V |
| VGS (th) (Max) @ Id | 3V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 17nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 470pF @ 20V |
| Antriebsspannung (Max Rds On, Min Rds On) | 10V |
| Vgs (Max) | ±20V |
| Verpackung | Cut Tape (CT) |
| Bleifreier Status / RoHS-Status | Lead free / RoHS Compliant |
| Feuchtigkeitsempfindlichkeitsniveau (MSL) | 1 (Unlimited) |
| Andere Namen | SI2319DS-T1-GE3CT |

SI2319DS-T1-GE3 ist neu im Original, Suche SI2319DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2319DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2319DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|---|---|--|---|
|  SI2320DS-T1-GE3 VISHAY SI2320DS-T1-GE3 VISHAY |  SI2320DS-T1 VISHAY SI2320DS-T1 VISHAY |  SI2319DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 40V 2.3A SOT23-3 |  SI2319DS 89K SI2319DS 89K |
|  SI2319CDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 40V 4.4A SOT-23 |  SI2320DS VISHAY SI2320DS VISHAY |  SI2319DDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CHAN 40V |  SI2319DS-T1-E3 Vishay / Siliconix MOSFET P-CH 40V 2.3A SOT23-3 |

heiße Teile

Mehr

- | | | | | |
|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊛ SI2316DS-T1-E3 | ↔ SI2316DS-T1-GE3 | ⇒ SI2316DS-T1-GE3 | D SI2317DS | ⇒ SI2317DS-T1-E3 |
| ⊣ SI2318ADS-T1-GE3 | ⊛ SI2318BDS-T1-E3 | D SI2318BDS-T1-GE3 | ⇒ SI2318CDS-T1-E3 | ⇒ SI2318CDS-T1-GE3 |
| ⊛ SI2318CDS-T1-GE3 | ⊣ SI2318DS | ⊛ SI2318DS-T1-E3 | ↔ SI2318DS-T1-E3 | ⇒ SI2318DS-T1-GE3 |
| D SI2318DS-T1-GE3 | ⊛ SI2319ADS-T1-GE3 | ⊣ SI2319C95TF | ⊛ SI2319CDS-T1-E3 | ⇒ SI2319CDS-T1-GE3 |
| ⇒ SI2319CDS-T1-GE3 | ↔ SI2319DDS-T1-GE3 | ⊛ SI2319DS | ⊣ SI2319DS-T1-E3 | ⇒ SI2319DS-T1-E3 |
| ↔ SI2319DS-T1-GE3 | ⇒ SI2320DS | D SI2320DS-T1-E3 | ⊛ SI2320DS-T1-GE3 | ⊣ SI2321DS-T1-E3 |
| ⊛ SI2321DS-T1-E3 | D SI2321DS-T1-GE3 | ⇒ SI2321DS-T1-GE3 | ↔ SI2323CDS-T1 | ⇒ SI2323CDS-T1-E3 |
| ⊣ SI2323CDS-T1-GE3 | ⊛ SI2323CDS-T1-GE3 | ↔ SI2323DDS-T1-E3 | ⇒ SI2323DDS-T1-GE3 | ⇒ SI2323DDS-T1-GE3 |
| ⊛ SI2323DS | ⊣ SI2323DS-T1-E3 | ⊛ SI2323DS-T1-E3 | D SI2323DS-T1-GE3 | ⇒ SI2323DS-T1-GE3 |
| ↔ SI2324DS-T1-E3 | ⊛ SI2324DS-T1-GE3 | ⊣ SI2324DS-T1-GE3 | ⊛ SI2325DS-T1-E3 | ⇒ SI2325DS-T1-E3 |

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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